



PJU1N60

600V N-Channel Enhancement Mode MOSFET

TO-251

FEATURES

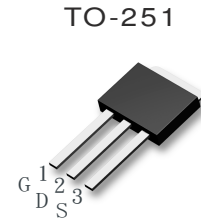
- 1A, 600V, $R_{DS(ON)}=11\Omega@V_{GS}=10V, I_D=0.5A$
- Low ON Resistance
- Fast Switching
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- Specially Designed for AC Adapter, Battery Charge and SMPS
- In compliance with EU RoHs 2002/95/EC Directives

MECHANICAL DATA

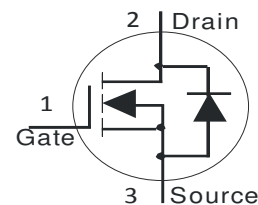
- Case: TO-220AB / TO-251 Molded Plastic
- Terminals : Solderable per MIL-STD-750, Method 2026

ORDERING INFORMATION

TYPE	MARKING	PACKAGE	PACKING
PJU1N60	U1N60	TO-251	80PCS/TUBE



INTERNAL SCHEMATIC DIAGRAM



Maximum RATINGS and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	Symbol	PJU1N60	Units
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	1	A
Pulsed Drain Current ¹⁾	I_{DM}	4.6	A
Maximum Power Dissipation Derating Factor	P_D	28 0.22	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Avalanche Energy with Single Pulse <small>$I_{AS}=1.1A, V_{DD}=50V, L=95mH$</small>	E_{AS}	58	mJ
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	4.5	$^\circ\text{C/W}$
Junction-to Ambient Thermal Resistance	$R_{\theta JA}$	100	$^\circ\text{C/W}$

Note : 1. Maximum DC current limited by the package

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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	600	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2.0	-	4.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =0.5A	-	8.3	11	Ω
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V	-	-	10	uA
Gate Body Leakage	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA
Dynamic						
Total Gate Charge	Q _g	V _{DS} =480V, I _D =1.0A V _{GS} =10V	-	6.2	7.8	nC
Gate-Source Charge	Q _{gs}		-	1.44	-	
Gate-Drain Charge	Q _{gd}		-	3.32	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} =300V, I _D =1.0A R _G =25Ω, V _{GS} =10V	-	10.2	14.8	ns
Turn-On Rise Time	t _r		-	5.6	8.0	
Turn-Off Delay Time	t _{d(off)}		-	16	22	
Turn-Off Fall Time	t _f		-	10.2	16	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V f=1.0MHz	-	165	220	pF
Output Capacitance	C _{oss}		-	17	28	
Reverse Transfer Capacitance	C _{rss}		-	1.65	4.2	
Source-Drain Diode						
Max. Diode Forward Current	I _S	-	-	-	1.0	A
Max.Pulsed Source Current	I _{SM}	-	-	-	4.6	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	-	1.5	V
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _F =1A di/dt=100A/us	-	190	-	ns
Reverse Recovery Charge	Q _{rr}		-	0.5	-	uC

NOTE : Plus Test: Pluse Width ≤ 300us, Duty Cycle ≤ 2%.



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Typical Characteristics Curves ($T_a=25^\circ\text{C}$, unless otherwise noted)

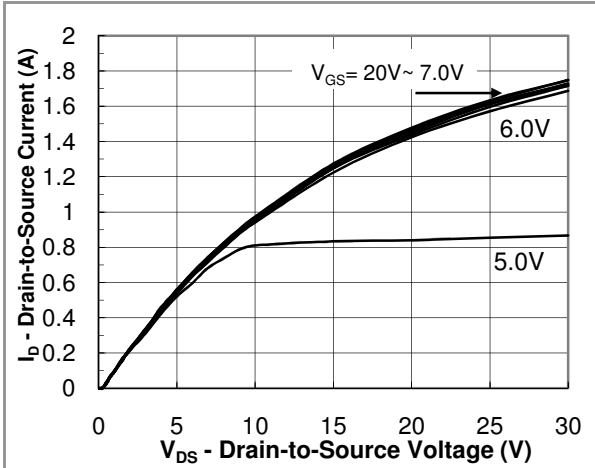


Fig.1 Output Characteristic

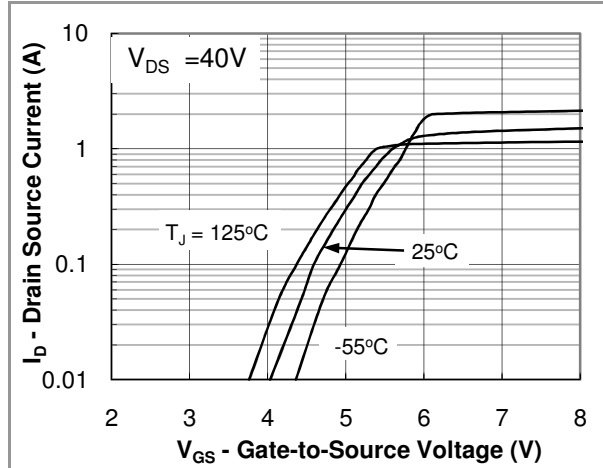


Fig.2 Transfer Characteristic

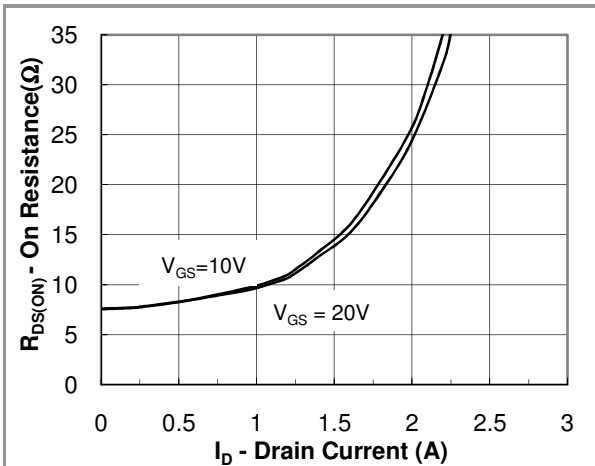


Fig.3 On Resistance vs Drain Current

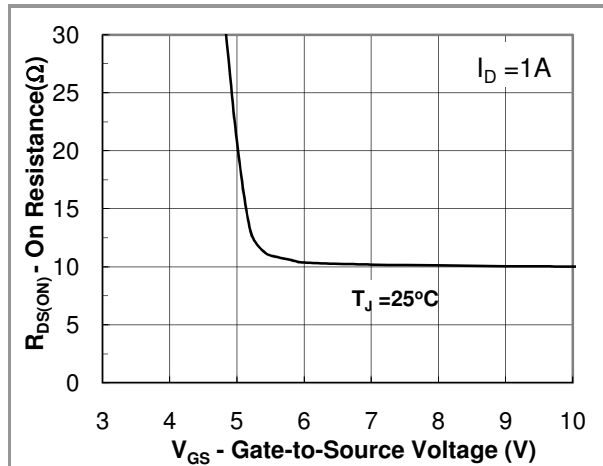


Fig.4 On Resistance vs Gate to Source Voltage

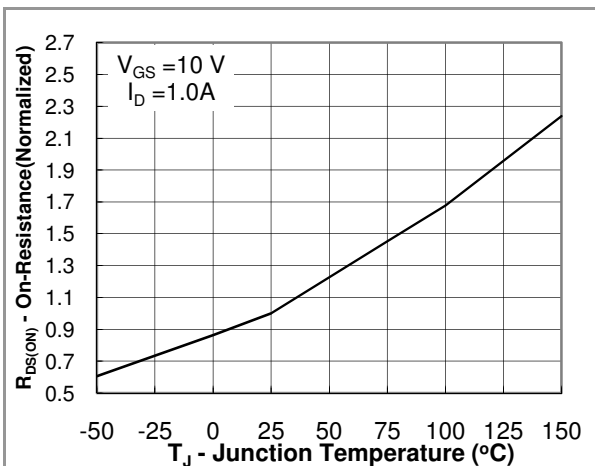


Fig.5 On Resistance vs Junction Temperature

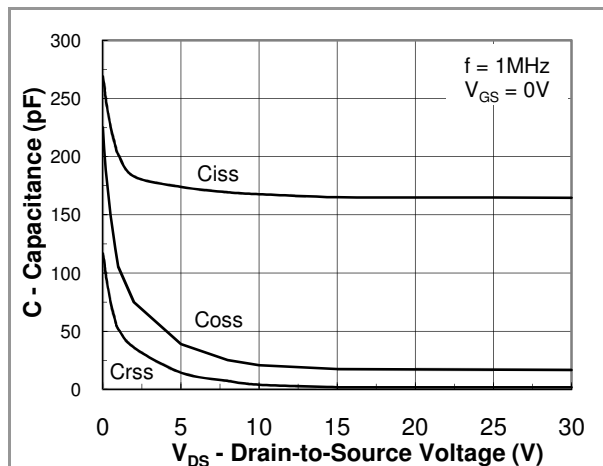


Fig.6 Capacitance



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Typical Characteristics Curves ($T_a=25^\circ\text{C}$, unless otherwise

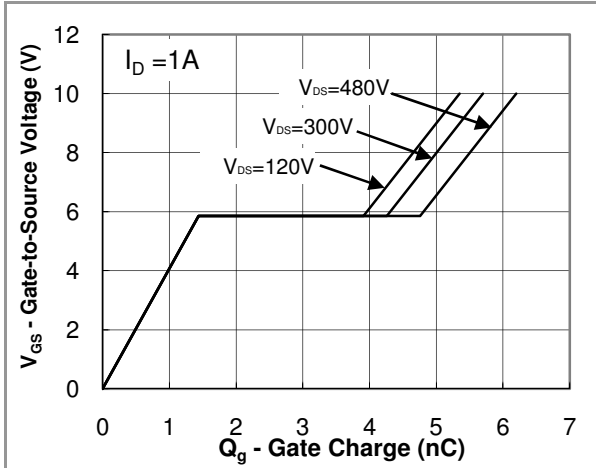


Fig. 7 Gate Charge Waveform

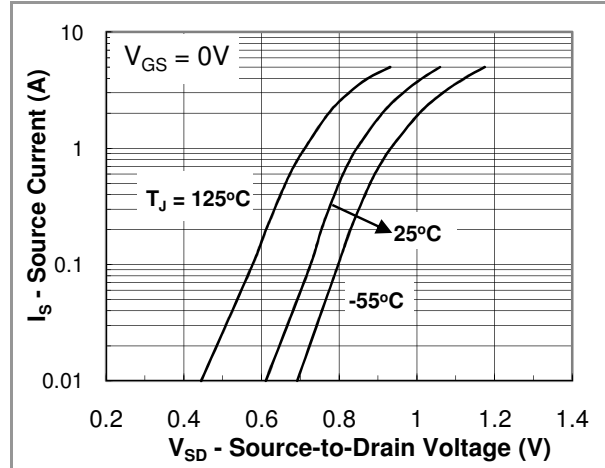


Fig.8 Source-Drain Diode Forward Voltage

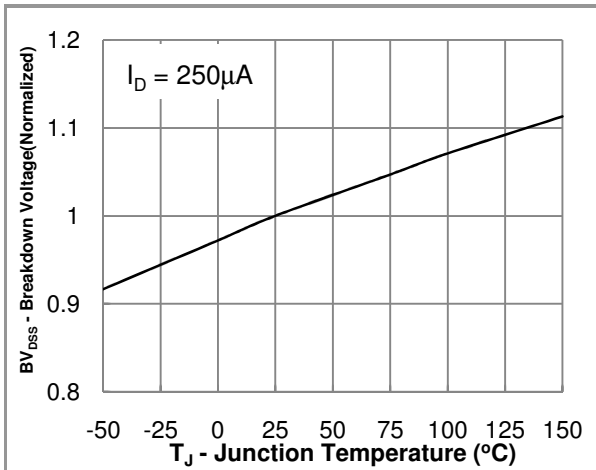


Fig.9 Breakdown Voltage vs Junction Temperature



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